December 1994

## 54F/74F38 Quad Two-Input NAND Buffer (Open Collector)

### **General Description**

This device contains four independent gates, each of which performs the logic NAND function. The open-collector outputs require external pull-up resistors for proper logical operation.

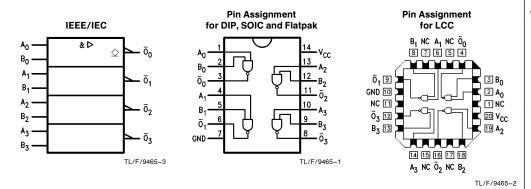
Commercial	Military	Package Number	Package Description
74F38PC		N14E	14-Lead (0.300" Wide) Molded Dual-In-Line
	54F38DM (Note 2)	J14A	14-Lead Ceramic Dual-In-Line
74F38SC (Note 1)		M14A	14-Lead (0.150" Wide) Molded Small Outline, JEDEC
74F38SJ (Note 1)		M14D	14-Lead (0.300" Wide) Molded Small Outline, EIAJ
	54F38FM (Note 2)	W14B	14-Lead Cerpack
	54F38LM (Note 2)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C

Note 1: Devices also available in 13" reel. Use suffix = SCX and SJX.

Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMQB, FMQB and LMQB.

### **Logic Symbol**

### **Connection Diagrams**



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# Unit Loading/Fan Out

			54F/74F				
Pin N	lames	Description	U.L. HIGH/LOW	Input I <sub>IH</sub> /I <sub>IL</sub> Output I <sub>OH</sub> /I <sub>OL</sub>			
A <sub>n</sub> , B	n	Inputs Outputs	1.0/2.0 OC*/106.6 (80)	20 μA/ – 1.2 mA OC*/64 mA (48 mA)			

<sup>\*</sup>OC = Open Collector

### **Function Table**

Inp	uts	Output			
Α	В	ō			
L	L	Н			
L	Н	Н			
Н	L	Н			
Н	Н	L			

H = HIGH Voltage Level

L = LOW Voltage Level

### **Absolute Maximum Ratings** (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 $\begin{array}{lll} \mbox{Storage Temperature} & -65^{\circ}\mbox{C to} + 150^{\circ}\mbox{C} \\ \mbox{Ambient Temperature under Bias} & -55^{\circ}\mbox{C to} + 125^{\circ}\mbox{C} \\ \mbox{Junction Temperature under Bias} & -55^{\circ}\mbox{C to} + 175^{\circ}\mbox{C} \\ \mbox{Plastic} & -55^{\circ}\mbox{C to} + 150^{\circ}\mbox{C} \\ \end{array}$ 

V<sub>CC</sub> Pin Potential to

Voltage Applied to Output

in HIGH State (with  $V_{CC} = 0V$ )

 $\begin{array}{lll} {\rm Standard\ Output} & -0.5{\rm V\ to\ V_{CC}} \\ {\rm TRI\text{-STATE}^{\circledast}\ Output} & -0.5{\rm V\ to\ } +5.5{\rm V} \end{array}$ 

Current Applied to Output

in LOW State (Max) twice the rated I<sub>OL</sub> (mA)

**Note 1:** Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

# Recommended Operating Conditions

Free Air Ambient Temperature

Military  $-55^{\circ}\text{C to} + 125^{\circ}\text{C}$ Commercial  $0^{\circ}\text{C to} + 70^{\circ}\text{C}$ 

Supply Voltage

Military + 4.5V to + 5.5V Commercial + 4.5V to + 5.5V

### **DC Electrical Characteristics**

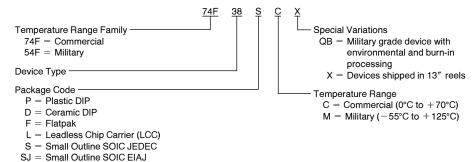
Symbol	Parameter		54F/74F			Units	v <sub>cc</sub>	Conditions	
Symbol			Min	Тур	Max	Onits	VCC	Conditions	
V <sub>IH</sub>	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal	
$V_{IL}$	Input LOW Voltage				0.8	V		Recognized as a LOW Signal	
$V_{CD}$	Input Clamp Diode Voltage				-1.2	V	Min	$I_{\text{IN}} = -18 \text{ mA}$	
V <sub>OL</sub>	Output LOW Voltage	54F 10% V <sub>CC</sub> 74F 10% V <sub>CC</sub>			0.55 0.55	٧	Min	$I_{OL} = 48 \text{ mA}$ $I_{OL} = 64 \text{ mA}$	
I <sub>IH</sub>	Input HIGH Current	54F 74F			20.0 5.0	μΑ	Max	$V_{\text{IN}} = 2.7V$	
I <sub>BVI</sub>	Input HIGH Current Breakdown Test	54F 74F			100 7.0	μΑ	Max	V <sub>IN</sub> = 7.0V	
$V_{ID}$	Input Leakage Test	74F	4.75			V	0.0	$I_{\text{ID}} = 1.9  \mu\text{A}$ All Other Pins Grounded	
I <sub>OD</sub>	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V <sub>IOD</sub> = 150 mV All Other Pins Grounded	
I <sub>IL</sub>	Input LOW Current				-1.2	mA	Max	$V_{IN} = 0.5V$	
I <sub>OHC</sub>	Open Collector, Output OFF Leakage Test				250	μΑ	Min	$V_{OUT} = V_{CC}$	
Icch	Power Supply Current			2.1	7.0	mA	Max	V <sub>O</sub> = HIGH	
I <sub>CCL</sub>	Power Supply Current			26.0	30.0	mA	Max	$V_O = LOW$	

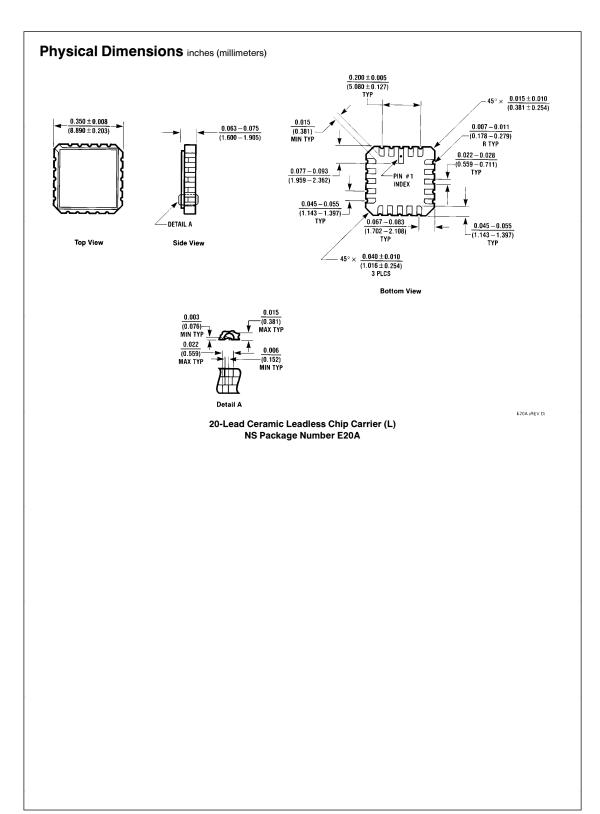
### **AC Electrical Characteristics**

	Parameter	$74F$ $T_A = +25^{\circ}C$ $V_{CC} = +5.0V$ $C_L = 50 \text{ pF}$			54F  T <sub>A</sub> , V <sub>CC</sub> = Mil  C <sub>L</sub> = 50 pF		$74F$ $T_{A}, V_{CC} = Com$ $C_{L} = 50 \text{ pF}$		Units
Symbol									
		Min	Тур	Max	Min	Max	Min	Max	
t <sub>PLH</sub>	Propagation Delay	6.5	9.7	12.5	6.5	14.5	6.5	13.0	ns
t <sub>PHL</sub>	$A_n$ , $B_n$ to $\overline{O}_n$	1.5	2.1	5.0	1.0	5.5	1.5	5.5	

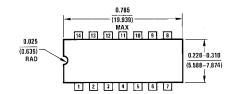
## **Ordering Information**

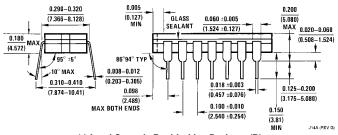
The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:



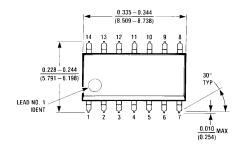


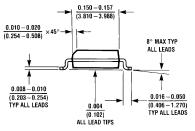


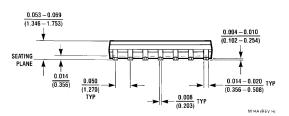




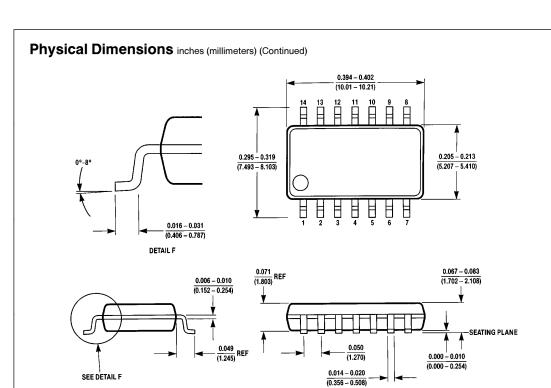
14-Lead Ceramic Dual-In-Line Package (D)
NS Package Number J14A





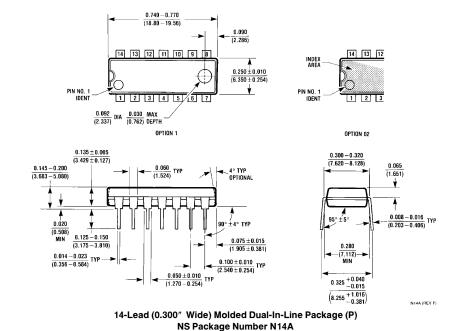


14-Lead (0.150" Wide) Molded Small Outline Package, JEDEC (S) NS Package Number M14A

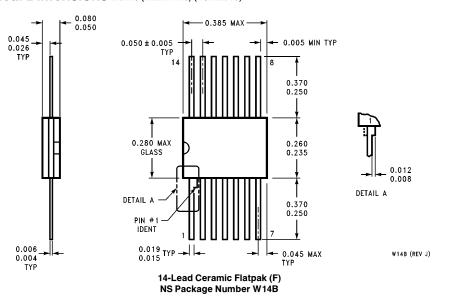


14-Lead (0.300" Wide) Molded Small Outline Package, EIAJ (SJ) NS Package Number M14D

M14D (REV A)



### Physical Dimensions inches (millimeters) (Continued)



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